



DCR390J85

Phase Control Thyristor

Replaces DS5833-4 DS5833-5 December 2024 (LN43773)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages VDRM and VRRM (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to 125°C,
DCR390J85*	8500	IDRM = IRRM = 100mA,
DCR390J80	8000	VDRM, VRRM tp = 10ms
DCR390J75	7500	VDSM & VRSM =
DCR390J70	7000	VDRM & VRRM + 100V
		respectively

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR390J85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	8500V
I _{T(AV)}	390A
Ітѕм	5250A
dV/dt*	1500V/µs
dl/dt	200A/μs

^{*}Higher dV/dt selections are available on request

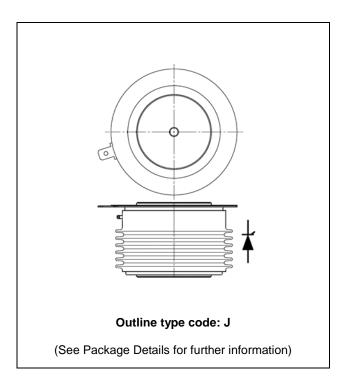


Fig. 1 Package outline

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^{*8200}V @ -40°C, 8500V @ 0°C



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
IT(AV)	Mean on-state current	Half wave resistive load	390	А
IT(RMS)	RMS value	-		А
lτ	Continuous (direct) on-state current	-	590	Α

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	5.25	kA
l²t	I2t for fusing	V _R = 0	0.14	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
	Thermal resistance - junction to case	Double side cooled	DC	-	37.8	°C/kW
Rth(j-c)		Single side cooled	Anode DC	-	74.3	°C/kW
			Cathode DC	-	79.5	°C/kW
D	Thermal resistance - case to heatsink	Clamping force 11.5kN (with mounting compound)	Double side	-	7.2	°C/kW
Rth(c-h)			Single side	-	14.4	°C/kW
Tvj	Virtual junction temperature	Blocking VDRM / VRRM		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			10	13	kN

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DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
IRRM/IDRM	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	;	-	100	mA
Vтм	Instantaneous forward voltage	At 1600A peak, Tj = 25°C		3.55	4.05	V
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 2x I _{T(AV)} Gate source 30V, 10Ω	Repetitive 50Hz	-	100	A/µs
	Trace of the of the state outlies.	tr < 0.5µs, Tj = 125°C	Non-repetitive	-	200	A/µs
V	Threshold voltage - Low level	100A to 400A at Tcase = 12	5°C	-	1.14	V
V т(то)	Threshold voltage - High level	400A to 1600A at Tcase = 125°C		-	1.32	V
	On-state slope resistance - Low level	100A to 400A at Tcase = 125°C		-	3.15	mΩ
ľΤ	On-state slope resistance - High level	400A to 1600A at Tcase = 125°C		-	2.73	mΩ
tgd	Delay time	V_D = 67% V_{DRM} , gate source 30V, 10Ω t_T = 0.5 μ s, T_j = 25°C		-	3	μs
tq	Turn-off time	Tj = 125°C, V _R = 100V, dl/dt = 5A/μs, dV _{DR} /dt = 20V/μs linear		-	1200	μs
Qs	Stored charge	Iτ = 500A, Tj = 125°C, dl/dt :	= 5A/µs	2000	3000	μC
IRR	Reverse recovery current	[LEM]		80	100	А
Qs	Stored charge	T _j = 125°C, dI/dt = 1A/μs, VR peak ~ 5000V, VR ~ 2800V		2050	3730	μC
IRR	Reverse recovery current			34	45	А
IL	Latching current	Tj = 25°C, VD = 5V		-	3	А
lн	Holding current	Tj = 25°C, Rg-κ = ∞, Iтм = 50	0A, Ιτ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V GT	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% VDRM, Tcase = 125°C	0.4	V
Igт	Gate trigger current	VDRM = 5V, Tcase = 25°C	350	mA
I GD	Gate non-trigger current	At 50% VDRM, Tcase = 125°C	15	mA

CURVES

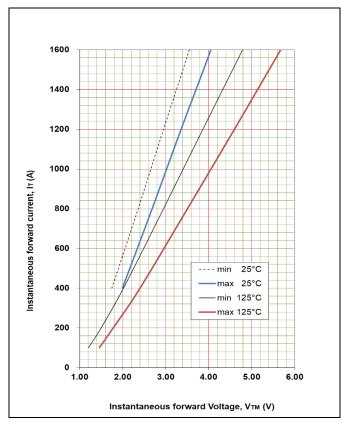


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

 $V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$

Where A = 0.690035

B = 0.110080

C = 0.002617

D = -0.000340

These values are valid for $T_j = 125$ °C for $I_T 100A$ to 1600A

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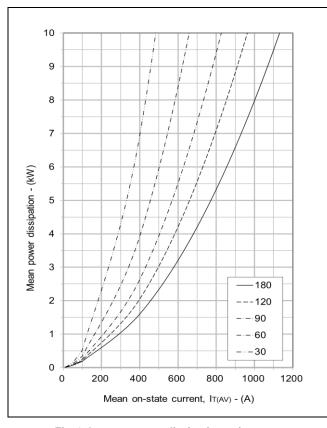


Fig. 3 On-state power dissipation - sine wave

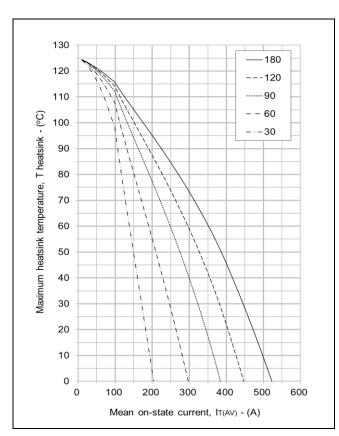


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

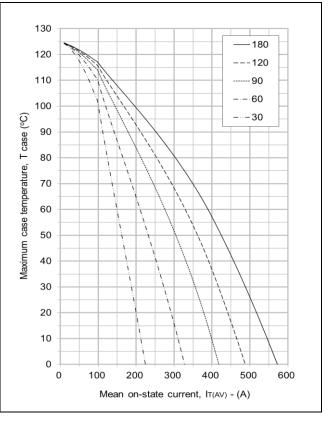


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

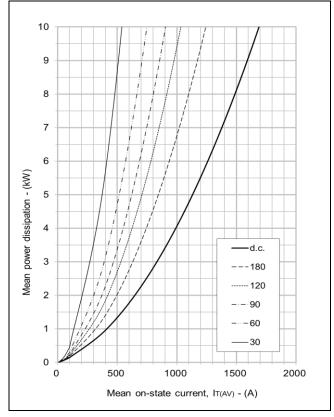


Fig. 6 On-state power dissipation - rectangular wave

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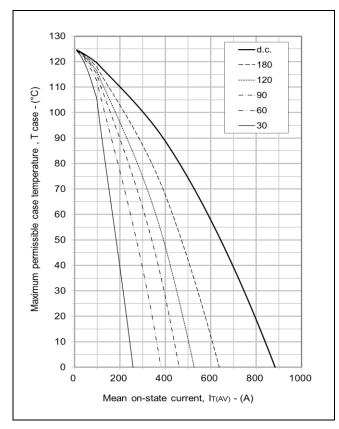
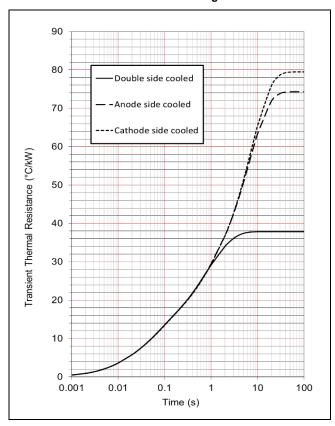


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



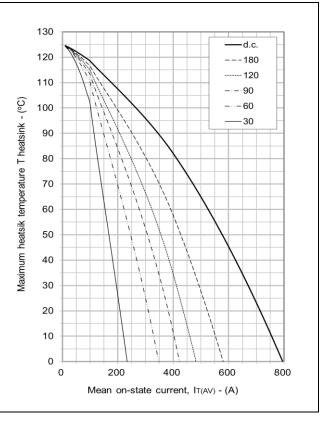


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	2.426	9.350	10.696	15.376
cooled	Ti(s)	0.009	0.053	0.450	1.395
Anode side	Ri(°C/kW)	2.809	9.558	11.356	50.614
cooled	Ti(s)	0.010	0.059	0.476	6.555
Cathode side	Ri(°C/kW)	2.951	9.403	11.077	56.041
cooled	Ti(s)	0.010	0.061	0.473	7.228

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

 $\Delta R_{\text{th(j-c)}}$ Conduction

Tables show the increments of thermal resistance R $_{\text{th}[j-c]}$ when the device operates at conduction angles other than d.c.

	Double side cooling				
	ΔZ _{th} (z)			
θ°	sine	rect			
180	4.43	3.01			
120	5.13	4.30			
90	5.89	5.03			
60	6.58	5.81			
30	7.12	6.67			
15	7.36	7 13			

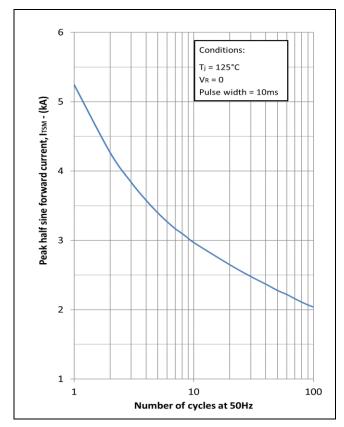
		Anode Side Cooling				
		ΔZ _{th} (z)				
	θ°	sine	rect			
	180	4.39	2.99			
	120	5.07	4.26			
	90	5.81	4.97			
	60	6 48	574			
	30	7.00	6.57			
	15	7.24	7.01			

L Ca	hode Sided Cooling				
	$\Delta Z_{th}(z)$				
e°	sine	rect			
180	4.37	2.98			
120	5.05	4.25			
90	5.79	4.96			
60	6.45	5.72			
30	6.97	6.54			
15	7.20	6.08			

Fig. 9 Maximum (limit) transient thermal impedance - junction to case (degC/kW)

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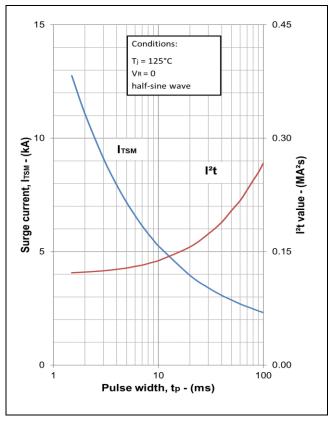


Fig. 10 Multi-cycle surge current

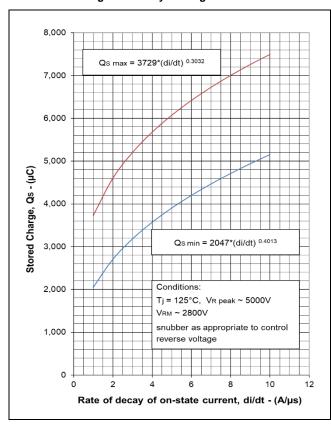


Fig. 12 Stored charge

Fig. 11 Single-cycle surge current

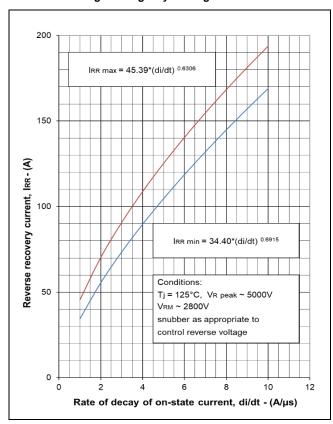


Fig. 13 Reverse recovery current

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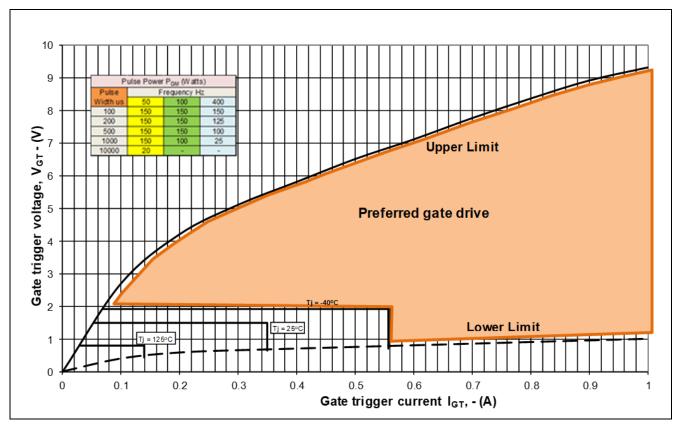


Fig. 14 Gate characteristics

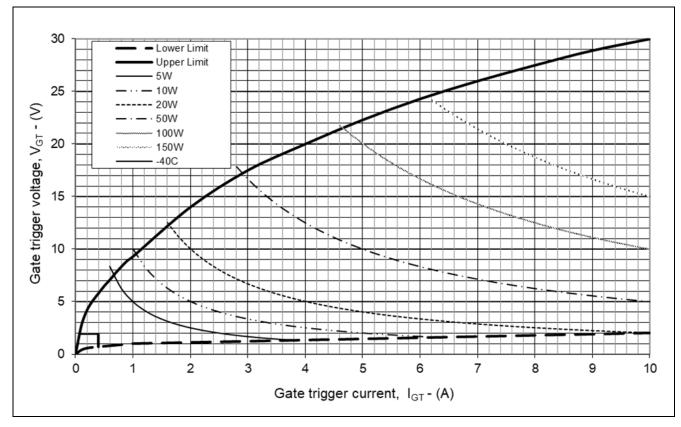


Fig. 15 Gate characteristics

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PACKAGE DETAILS

For further package information, please contact Customer services.

All dimensions in mm, unless stated otherwise.

DO NOT SCALE

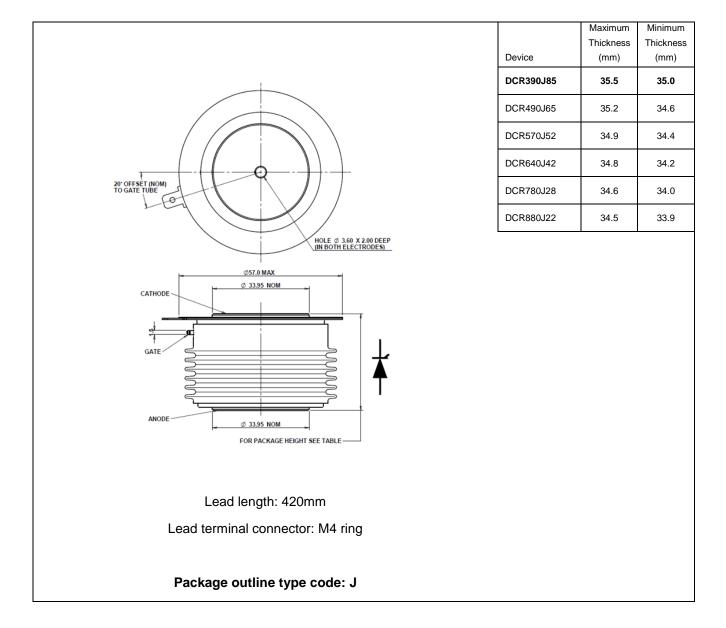


Fig. 16 Package outline

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